



3DD12

NPN Silicon Low Frequency High Power Transistor



Features:

1. Using triple-diffusion process.Excellent capacity in anti-burnout.Excellent second breakdown capacity.
2. Good temperature stability.Excellent thermal fatigue capability.
3. Implementation of standards: QZJ840611
4. Use for Low-speed switch,low frequency power amplify,power adjustment.
5. Quality Class: General, GS

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications									Test Condition
			A	B	C	D	E	F	G	H	I	
Collector-Emitter Voltage	V _{CEO}	V	50	100	150	200	250	300	400	500	600	
Emitter-Base Voltage	V _{EBO}	V	3									
Max. Collector Current	I _{CM}	A	A~F:50, G~I:25									
Max. Collector Dissipation	P _{CM}	W	500									Tc:75°C
Junction Temperature	T _{jm}	°C	175									
Storage Temperature	T _{stg}	°C	-55~+175									
Collector-Emitter Leakage Current	I _{CEO}	mA	Max.:10.0									A:V _{CE} =30V;B:V _{CE} =50V; C~I:V _{CE} =100V
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	Max.:3.0									A~F: I _C =25A, I _B =5A
												G~I: I _C =15A, I _B =3A
DC Current Gain	h _{FE}		Min.:10									A~F: V _{CE} =10V, I _C =25A
												G~I:V _{CE} =10V, I _C =15A
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	V	A	B	C	D	E	F	G	H	I	I _C =10mA
			50	100	150	200	250	300	400	500	600	
E-Base Breakdown Voltage	V _{(BR)EBO}	V	3									I _E =20mA

h_{FE} Colored:

Color	Red	Yellow	Green	Black	White
h _{FE}	10~20	20~30	30~50	50~80	>80

Outline and Dimensions: